

FDD8796/FDU8796

N-Channel PowerTrench® MOSFET

25V, 35A, 5.7mΩ



General Description

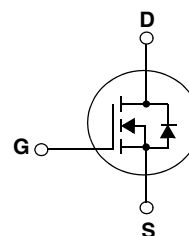
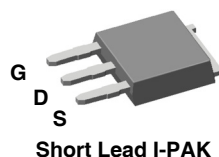
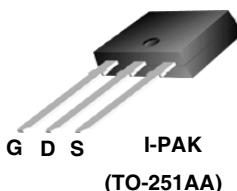
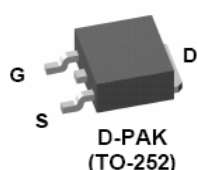
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(on)}$ and fast switching speed.

Features

- Max $r_{DS(on)}$ = 5.7mΩ at V_{GS} = 10V, I_D = 35A
- Max $r_{DS(on)}$ = 8.0mΩ at V_{GS} = 4.5V, I_D = 35A
- Low gate charge: $Q_{g(10)}$ = 37nC(Typ), V_{GS} = 10V
- Low gate resistance
- Avalanche rated and 100% tested
- RoHS Compliant

Application

- Vcore DC-DC for Desktop Computers and Servers
- VRM for Intermediate Bus Architecture



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current -Continuous (Package Limited)	35	A
	-Continuous (Die Limited)	98	
	-Pulsed (Note 1)	305	
E_{AS}	Single Pulse Avalanche Energy (Note 2)	91	mJ
P_D	Power Dissipation	88	W
T_J, T_{STG}	Operating and Storage Temperature	-55 to 175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case TO_252, TO_251	1.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient TO_252, TO_251	100	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient TO-252, 1in ² copper pad area	52	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8796	FDD8796	TO-252AA	13"	12mm	2500 units
FDU8796	FDU8796	TO-251AA	N/A (Tube)	N/A	75 units
FDU8796	FDU8796_F071	TO-251AA	N/A (Tube)	N/A	75 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
B_{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	25			V
$\frac{\Delta B_{VDSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		7		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 20\text{V}$ $V_{GS} = 0\text{V}$ $T_J = 150^\circ\text{C}$			1 250	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	1.2	1.8	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		-6.7		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 35\text{A}$		4.5	5.7	m Ω
		$V_{GS} = 4.5\text{V}$, $I_D = 35\text{A}$		6.0	8.0	
		$V_{DS} = 10\text{V}$, $I_D = 35\text{A}$ $T_J = 175^\circ\text{C}$		6.9	9.5	

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 13\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		1960	2610	pF
C_{oss}	Output Capacitance			455	605	pF
C_{rss}	Reverse Transfer Capacitance			315	475	pF
R_G	Gate Resistance	$f = 1\text{MHz}$		1.1		Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 13\text{V}$, $I_D = 35\text{A}$ $V_{GS} = 10\text{V}$, $R_{GS} = 20\Omega$		10	20	ns
t_r	Rise Time			24	39	ns
$t_{d(off)}$	Turn-Off Delay Time			99	158	ns
t_f	Fall Time	$V_{DD} = 13\text{V}$, $I_D = 35\text{A}$, $I_g = 1.0\text{mA}$		57	91	ns
Q_g	Total Gate Charge		$V_{GS} = 0$ to 10V	37	52	nC
Q_g	Total Gate Charge		$V_{GS} = 0$ to 5V	19	27	nC
Q_{gs}	Gate to Source Gate Charge			6		nC
Q_{gd}	Gate to Drain Charge			6		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$V_{GS} = 0\text{V}$, $I_S = 35\text{A}$		0.9	1.25	V
		$V_{GS} = 0\text{V}$, $I_S = 15\text{A}$		0.8	1.0	V
t_{rr}	Reverse Recovery Time	$I_F = 35\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$		30	45	ns
Q_{rr}	Reverse Recovery Charge	$I_F = 35\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$		23	35	nC

Notes:

- 1: Pulse time $< 300\mu\text{s}$, Duty cycle = 2%.
 2: Starting $T_J = 25^\circ\text{C}$, $L = 0.3\text{mH}$, $I_{AS} = 24.7\text{A}$, $V_{DD} = 23\text{V}$, $V_{GS} = 10\text{V}$.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

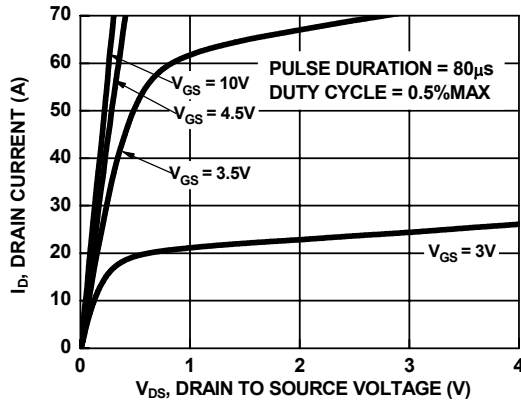


Figure 1. On Region Characteristics

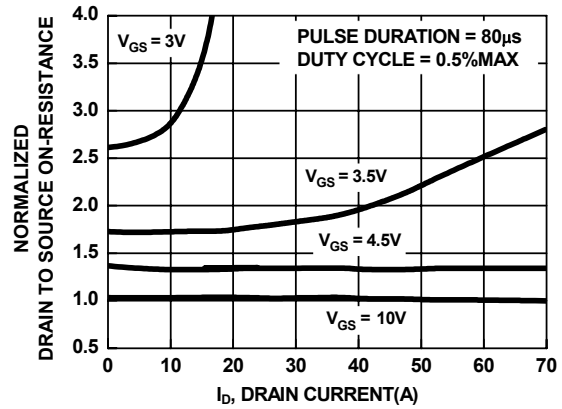


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

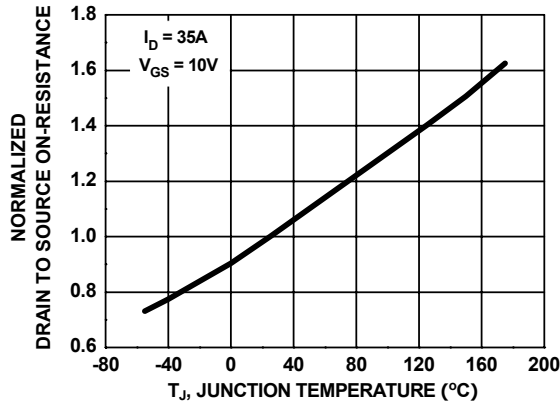


Figure 3. Normalized On Resistance vs Junction Temperature

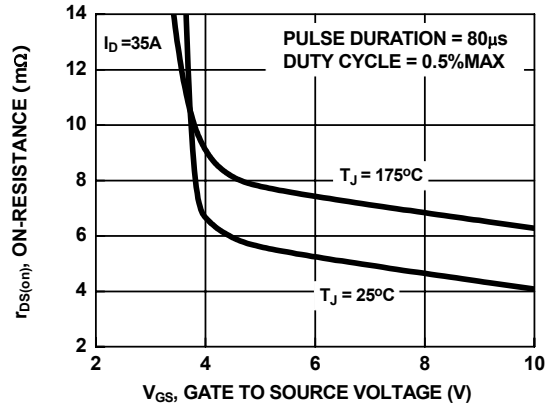


Figure 4. On-Resistance vs Gate to Source Voltage

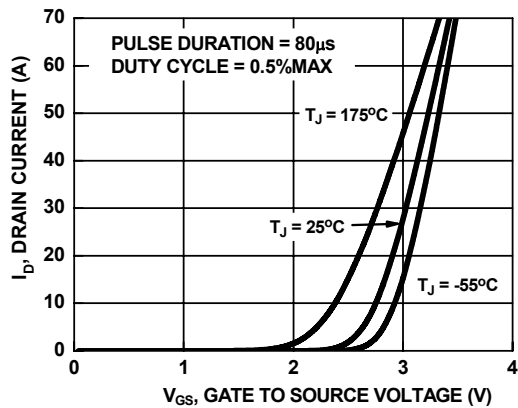


Figure 5. Transfer Characteristics

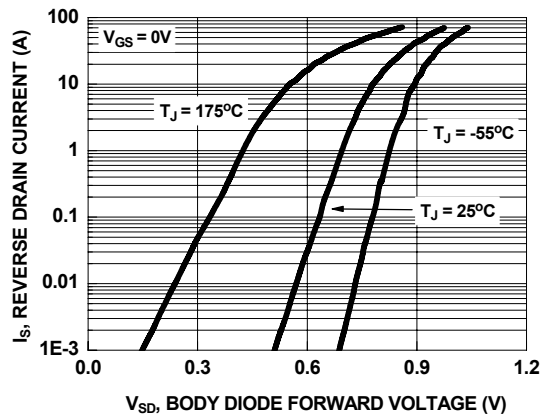


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

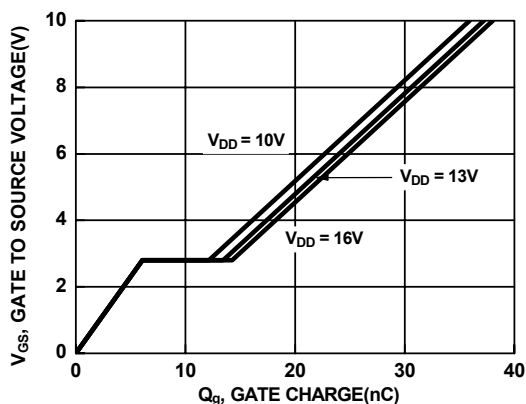


Figure 7. Gate Charge Characteristics

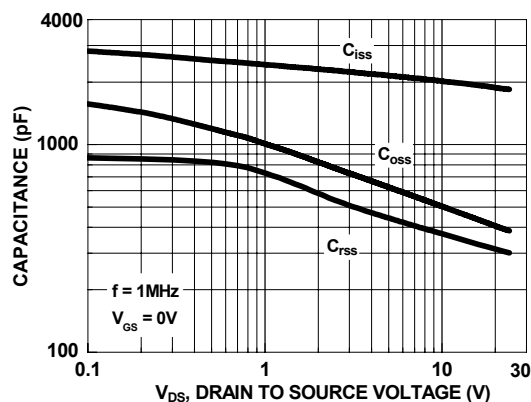


Figure 8. Capacitance vs Drain to Source Voltage

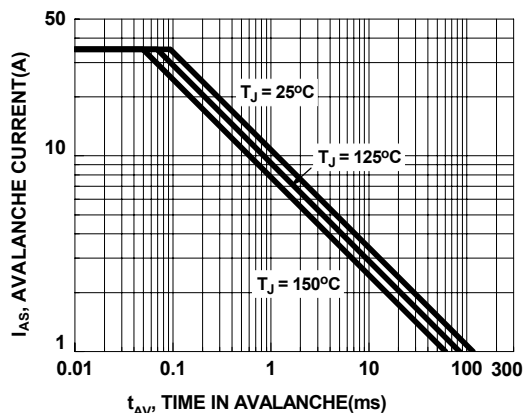


Figure 9. Unclamped Inductive Switching Capability

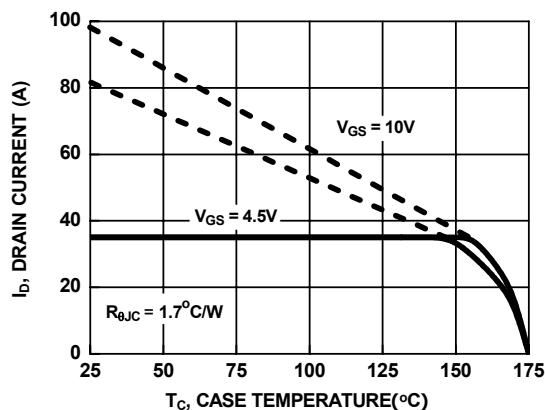


Figure 10. Maximum Continuous Drain Current vs Case Temperature

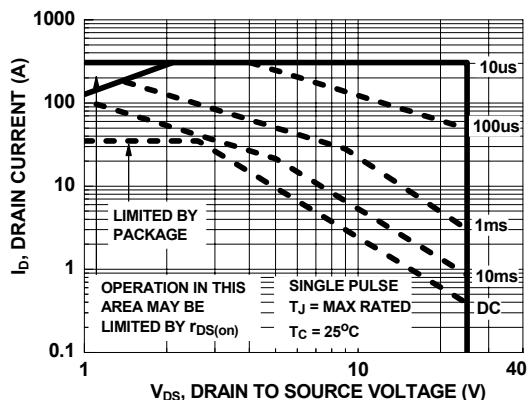


Figure 11. Forward Bias Safe Operating Area

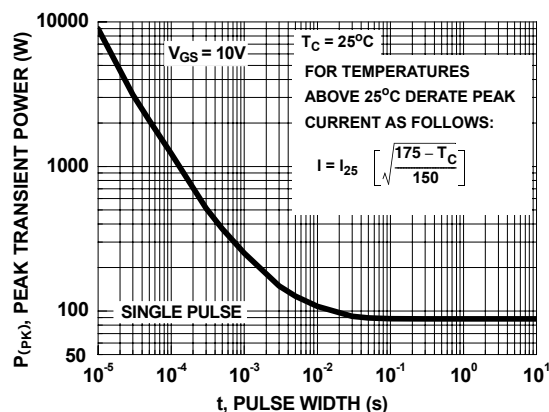
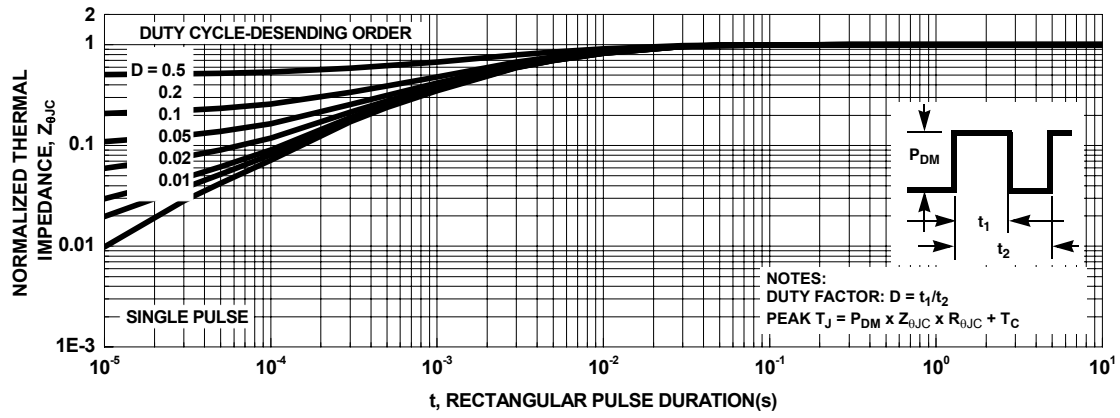


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE ^x ™	FAST [®]	ISOPLANAR™	PowerSaver™	SuperSOT™-6
ActiveArray™	FAST ^r ™	LittleFET™	PowerTrench [®]	SuperSOT™-8
Bottomless™	FPS™	MICROCOUPLER™	QFET [®]	SyncFET™
Build it Now™	FRFET™	MicroFET™	QS™	TCM™
CoolFET™	GlobalOptoisolator™	MicroPak™	QT Optoelectronics™	TinyLogic [®]
CROSSVOLT™	GTO™	MICROWIRE™	Quiet Series™	TINYOPTO™
DOME™	HiSeC™	MSX™	RapidConfigure™	TruTranslation™
EcoSPARK™	I ² C™	MSXPro™	RapidConnect™	UHC™
E ² CMOS™	i-Lo™	OCX™	μSerDes™	UltraFET [®]
EnSigna™	ImpliedDisconnect™	OCXPro™	ScalarPump™	UniFET™
FACT™	IntelliMAX™	OPTOLOGIC [®]	SILENT SWITCHER [®]	VCX™
FACT Quiet Series™		OPTOPLANAR™	SMART START™	Wire™
		PACMAN™	SPM™	
Across the board. Around the world.™		POP™	Stealth™	
The Power Franchise [®]		Power247™	SuperFET™	
Programmable Active Droop™		PowerEdge™	SuperSOT™-3	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS**Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. 118

Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели,
кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



Телефон: 8 (812) 309-75-97 (многоканальный)

Факс: 8 (812) 320-03-32

Электронная почта: ocean@oceanchips.ru

Web: <http://oceanchips.ru/>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, д. 2, корп. 4, лит. А